

BCR3AS-12B

600V - 3A - Triac

Low Power Use

R07DS1439EJ0500
 (Previous: REJ03G0450-0400)
 Rev.5.00
 May. 10, 2019

Features

- $I_{T(RMS)}$: 3 A
- V_{DRM} : 600 V
- I_{FGT} , I_{RGT} , $I_{RGT III}$: 15 mA
- T_j : 150 °C
- Planar Passivation Type

Outline

RENESAS Package code: PRSS0004ZG-A
 (Package name: MP-3A)

1. T₁ Terminal
 2. T₂ Terminal
 3. Gate Terminal
 4. T₂ Terminal

Application

Small motor control, heater control, and other general purpose AC control applications.

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Notes: 1. Gate open.

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	3	A	Commercial frequency, sine full wave 360°conduction, $T_c = 133^{\circ}C$ ^{Note3}
Surge on-state current	I_{TSM}	30	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	3.7	A ² s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	P_{GM}	3	W	
Average gate power dissipation	$P_{G(AV)}$	0.3	W	
Peak gate voltage	V_{GM}	6	V	
Peak gate current	I_{GM}	0.3	A	
Junction Temperature	T_j	-40 to +150	°C	
Storage temperature	T_{stg}	-40 to +150	°C	

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 150^\circ\text{C}$, V_{DRM} applied	
On-state voltage	V_{TM}	—	—	1.7	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 4.5\text{ A}$, instantaneous measurement	
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	15	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	15	mA	
	III	I_{RGTIII}	—	—	15	mA	
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$	
		0.1	—	—		$T_j = 150^\circ\text{C}$, $V_D = 1/2 V_{DRM}$	
Thermal resistance	$R_{th(j-c)}$	—	—	3.8	$^\circ\text{C/W}$	Junction to case ^{Note3}	
Critical-rate of rise of off-state commutating voltage ^{Note4}	$(dv/dt)_c$	5	—	—	V/ μs	$T_j = 125^\circ\text{C}$	
		1	—	—		$T_j = 150^\circ\text{C}$	

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured on the T_2 tab.

4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -1.5\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	